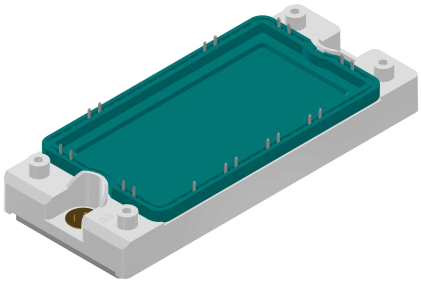
Standard Rectifier Module

3~ Rectifier		Brake Chopper	
V_{RRM} =	1600 V	V_{CES} =	1200 V
I_{DAV} =	150 A	I_{C25} =	180 A
I_{FSM} =	1100 A	$V_{CE(sat)}$ =	1.7 V

3~ Rectifier Bridge + Brake Unit + NTC

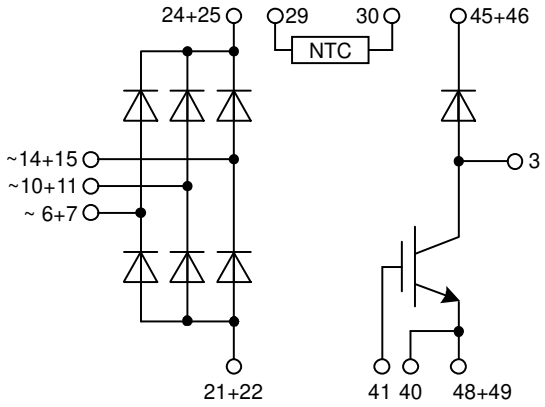
Part number

VUB145-16NOXT



Backside: isolated

E72873



Features / Advantages:

- Package with DCB ceramic
- Improved temperature and power cycling
- Planar passivated chips
- Very low forward voltage drop
- Very low leakage current
- NTC
- X2PT - 2nd generation Xtreme light Punch Through
- Rugged X2PT design results in:
  - short circuit rated for 10 µsec.
  - very low gate charge
  - low EMI
  - square RBSOA @ 2x Ic
- Thin wafer technology combined with X2PT design results in a competitive low VCE(sat) and low thermal resistance

Applications:

- 3~ Rectifier with brake unit for drive inverters

Package: E2-Pack

- Isolation Voltage: 3600 V~
- Industry standard outline
- RoHS compliant
- Soldering pins for PCB mounting
- Height: 17 mm
- Base plate: Copper internally DCB isolated
- Advanced power cycling
- Phase Change Material available

Disclaimer Notice

Information furnished is believed to be accurate and reliable. However, users should independently evaluate the suitability of and test each product selected for their own applications. Littelfuse products are not designed for, and may not be used in, all applications. Read complete Disclaimer Notice at www.littelfuse.com/disclaimer-electronics.

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Rectifier

Symbol	Definition	Conditions		Ratings min.	typ.	max.	Unit
V_{RSM}	*max. non-repetitive reverse blocking voltage*		T_{VJ} = 25°C			1700	V
V_{RRM}	*max. repetitive reverse blocking voltage*		T_{VJ} = 25°C			1600	V
I_R	*reverse current*	V_R = 1600 V	T_{VJ} = 25°C			100	µA
		V_R = 1600 V	T_{VJ} = 150°C			2	mA
V_F	*forward voltage drop*	I_F = 50 A	T_{VJ} = 25°C			1.20	V
		I_F = 150 A				1.68	V
		I_F = 50 A	T_{VJ} = 125°C			1.13	V
		I_F = 150 A				1.74	V
I_{DAV}	*bridge output current*	T_C = 105°C	T_{VJ} = 150°C			150	A
		rectangular d = ⅓					
V_{F0}	*threshold voltage* } *for power loss calculation only*		T_{VJ} = 150°C			0.87	V
r_F	*slope resistance* }					5.9	mΩ
R_{thJC}	*thermal resistance junction to case*					0.5	K/W
R_{thCH}	*thermal resistance case to heatsink*				0.1		K/W
P_{tot}	*total power dissipation*		T_C = 25°C			250	W
I_{FSM}	*max. forward surge current*	t = 10 ms; (50 Hz), sine	T_{VJ} = 45°C			1.10	kA
		t = 8,3 ms; (60 Hz), sine	V_R = 0 V			1.19	kA
		t = 10 ms; (50 Hz), sine	T_{VJ} = 150°C			935	A
		t = 8,3 ms; (60 Hz), sine	V_R = 0 V			1.01	kA
I^2t	*value for fusing*	t = 10 ms; (50 Hz), sine	T_{VJ} = 45°C			6.05	kA²s
		t = 8,3 ms; (60 Hz), sine	V_R = 0 V			5.89	kA²s
		t = 10 ms; (50 Hz), sine	T_{VJ} = 150°C			4.37	kA²s
		t = 8,3 ms; (60 Hz), sine	V_R = 0 V			4.25	kA²s
C_J	*junction capacitance*	V_R = 400 V; f = 1 MHz	T_{VJ} = 25°C		37		pF

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Brake IGBT + Diode				Ratings			
Symbol	**Definition**	**Conditions**		**min.**	**typ.**	**max.**	**Unit**
V_{CES}	*collector emitter voltage*		T_{VJ} = 25°C			1200	V
V_{GES}	*max. DC gate voltage*					±20	V
V_{GEM}	*max. transient gate emitter voltage*					±30	V
I_{C25}	*collector current*		T_C = 25°C			180	A
I_{C80}			T_C = 80°C			140	A
P_{tot}	*total power dissipation*		T_C = 25°C			500	W
$V_{CE(sat)}$	*collector emitter saturation voltage*	I_C = 100 A; V_{GE} = 15 V	T_{VJ} = 25°C		1.7	2.1	V
			T_{VJ} = 125°C		1.9		V
$V_{GE(th)}$	*gate emitter threshold voltage*	I_C = 4 mA; V_{GE} = V_{CE}	T_{VJ} = 25°C	6	6.8	7.5	V
I_{CES}	*collector emitter leakage current*	V_{CE} = V_{CES}; V_{GE} = 0 V	T_{VJ} = 25°C			0.1	mA
			T_{VJ} = 125°C		0.1		mA
I_{GES}	*gate emitter leakage current*	V_{GE} = ±20 V				500	nA
$Q_{G(on)}$	*total gate charge*	V_{CE} = 600 V; V_{GE} = 15 V; I_C = 100 A			340		nC
$t_{d(on)}$	*turn-on delay time*	inductive load V_{CE} = 600 V; I_C = 100 A V_{GE} = ±15 V; R_G = 6.8 Ω	T_{VJ} = 125°C		230		ns
t_r	*current rise time*				70		ns
$t_{d(off)}$	*turn-off delay time*				380		ns
t_f	*current fall time*				230		ns
E_{on}	*turn-on energy per pulse*				12.5		mJ
E_{off}	*turn-off energy per pulse*				11.5		mJ
RBSOA	*reverse bias safe operating area*	V_{GE} = ±15 V; R_G = 6.8 Ω	T_{VJ} = 125°C				
I_{CM}		V_{CEK} = 1200 V				300	A
SCSOA	*short circuit safe operating area*	V_{CEK} = 1200 V					
t_{SC}	*short circuit duration*	V_{CE} = 720 V; V_{GE} = ±15	T_{VJ} = 125°C			10	µs
I_{SC}	*short circuit current*	R_G = 6.8 Ω; non-repetitive			450		A
R_{thJC}	*thermal resistance junction to case*					0.25	K/W
R_{thCH}	*thermal resistance case to heatsink*				0.1		K/W

Brake Diode							
V_{RRM}	*max. repetitive reverse voltage*		T_{VJ} = 25°C			1200	V
I_{F25}	*forward current*		T_C = 25°C			48	A
I_{F80}			T_C = 80°C			32	A
V_F	*forward voltage*	I_F = 30 A	T_{VJ} = 25°C			2.75	V
			T_{VJ} = 125°C		1.60		V
I_R	*reverse current*	V_R = V_{RRM}	T_{VJ} = 25°C			0.25	mA
			T_{VJ} = 125°C			1	mA
Q_{rr}	*reverse recovery charge*	V_R = 600 V $-di_F/dt$ = 1000 A/µs I_F = 30 A; V_{GE} = 0 V	T_{VJ} = 125°C		5.2		µC
I_{RM}	*max. reverse recovery current*				50		A
t_{rr}	*reverse recovery time*				300		ns
E_{rec}	*reverse recovery energy*				1.9		mJ
R_{thJC}	*thermal resistance junction to case*					0.9	K/W
R_{thCH}	*thermal resistance case to heatsink*				0.1		K/W

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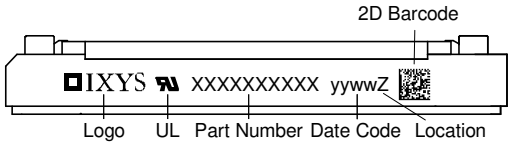
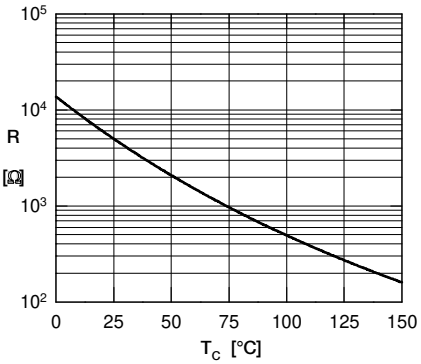
Package E2-Pack				Ratings			
Symbol	**Definition**	**Conditions**		**min.**	**typ.**	**max.**	**Unit**
I_{RMS}	*RMS current*	per terminal				50	A
T_{VJ}	*virtual junction temperature*			-40		150	°C
T_{op}	*operation temperature*			-40		125	°C
T_{stg}	*storage temperature*			-40		125	°C
Weight					176		g
M_D	*mounting torque*			3		6	Nm
$d_{Spp/App}$	*creepage distance on surface | striking distance through air*		*terminal to terminal*	6.0			mm
$d_{Spb/Apb}$			*terminal to backside*	12.0			mm
V_{ISOL}	*isolation voltage*	t = 1 second	50/60 Hz, RMS; I_{ISOL} ≤ 1 mA	3600			V
		t = 1 minute		3000			V



Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	VUB145-16NOXT	VUB145-16NOXT	Box	6	521635

Temperature Sensor NTC

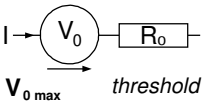
Symbol	Definition	Conditions	min.	typ.	max.	Unit
R_{25}	*resistance*	T_{VJ} = 25°	4.75	5	5.25	kΩ
$B_{25/50}$	*temperature coefficient*			3375		K



Typ. NTC resistance vs. temperature

Equivalent Circuits for Simulation

** on die level* T_{VJ} = 150°C



		Rectifier	Brake Diode	
$V_{0\ max}$	*threshold voltage*	0.87	1.31	V
$R_{0\ max}$	*slope resistance **	3.3	8	mΩ

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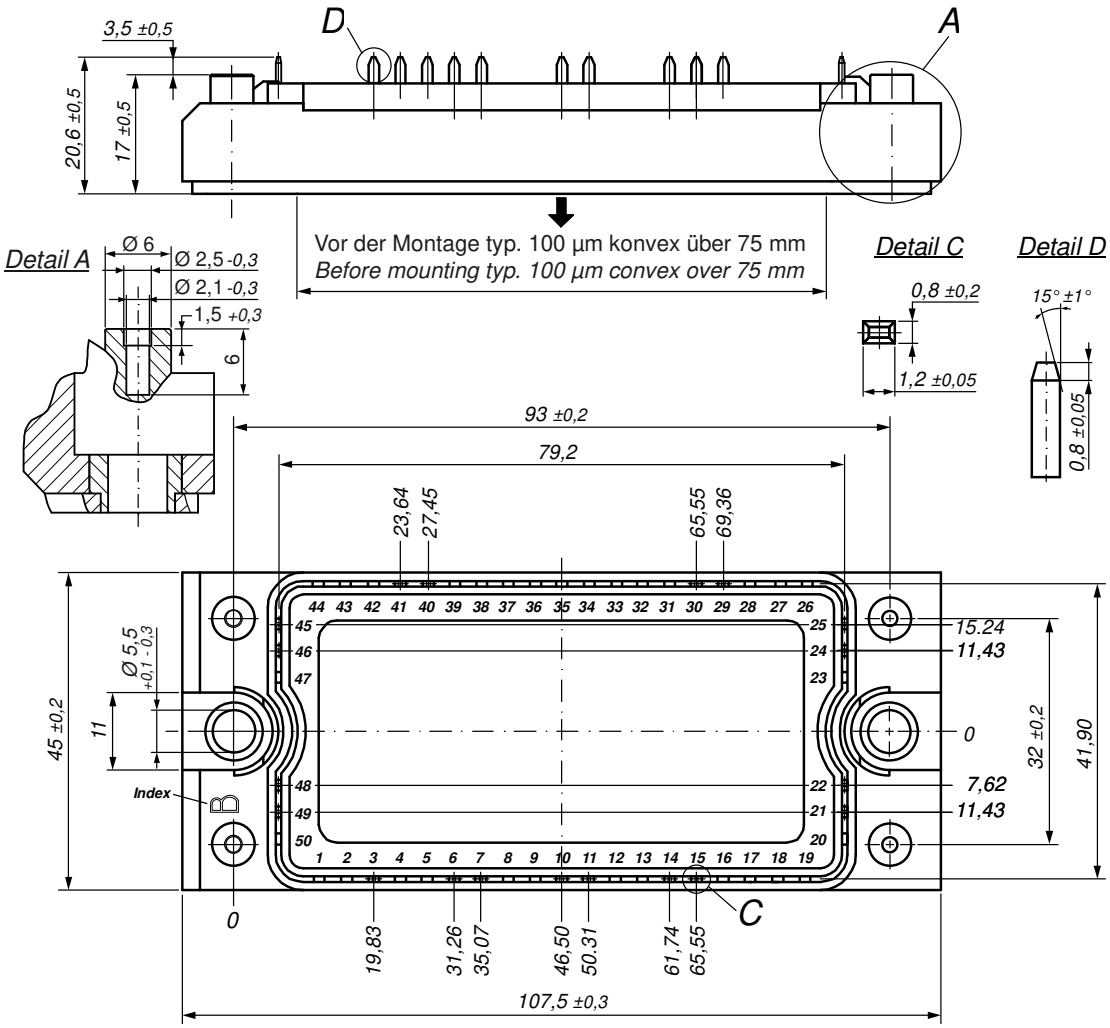
Outlines E2-Pack

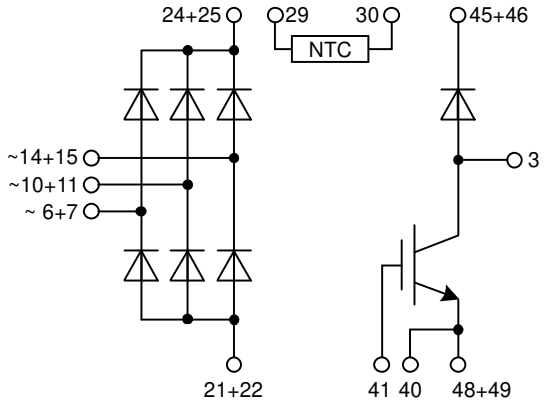


Bemerkung / ***Note:***

- Nichttolerierte Maße nach / *Measure without tolerances according DIN ISO 2768-T1-m*
- PCB-Lochmuster / *PCB hole pattern:* **see pin position**
- Toleranz Pin-Position und PCB-Lochmuster / *Tolerance of pin position and PCB hole pattern:* ⌖ **0.1**
- Montageanleitung / *Mounting instruction:* www.ixys.com **Application note IXAN0024**

***Detail A*:** PCB-Montage / *Mounting on PCB*

- Empfohlene, selbstschneidende Schraube / *Recommended, self-tapping screw:* **EJOT PT®** (Größe / *size:* **K25**)
- Max. Schraubenlänge / *Max. screw length:* **PCB-Dicke** / **thickness + 6 mm** *(*max. Lochtiefe / *hole depth)*
- Empfohlenes Drehmoment / *Recommended mounting torque:* **1.5 Nm**



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Rectifier

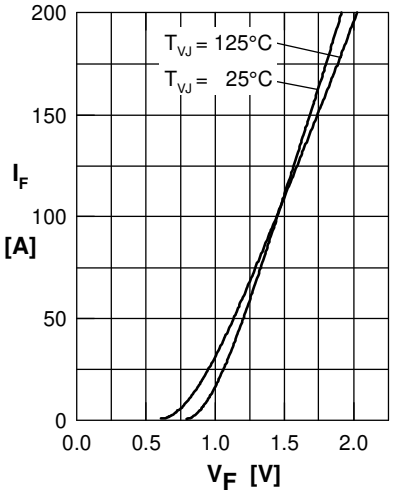

Fig. 1 Forward current vs. voltage drop per diode

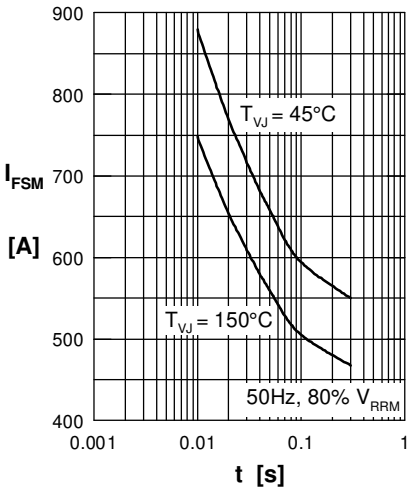

Fig. 2 Surge overload current vs. time per diode

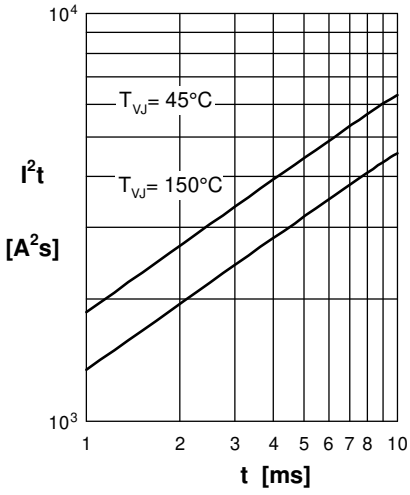

Fig. 3 I^2t vs. time per diode

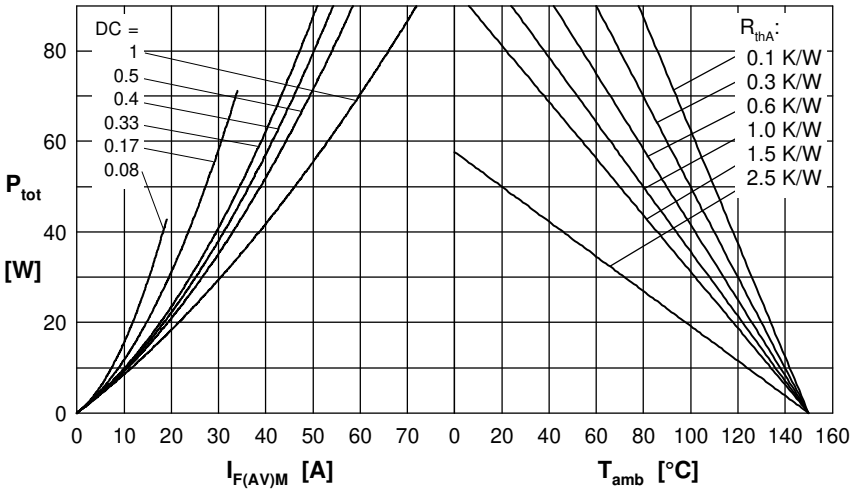

Fig. 4 Power dissipation vs. forward current and ambient temperature per diode

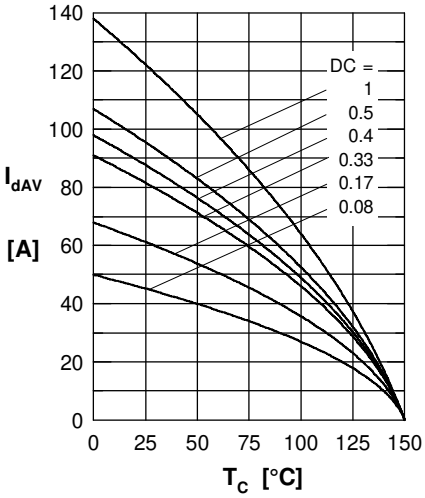

Fig. 5 Max. forward current vs. case temperature per diode

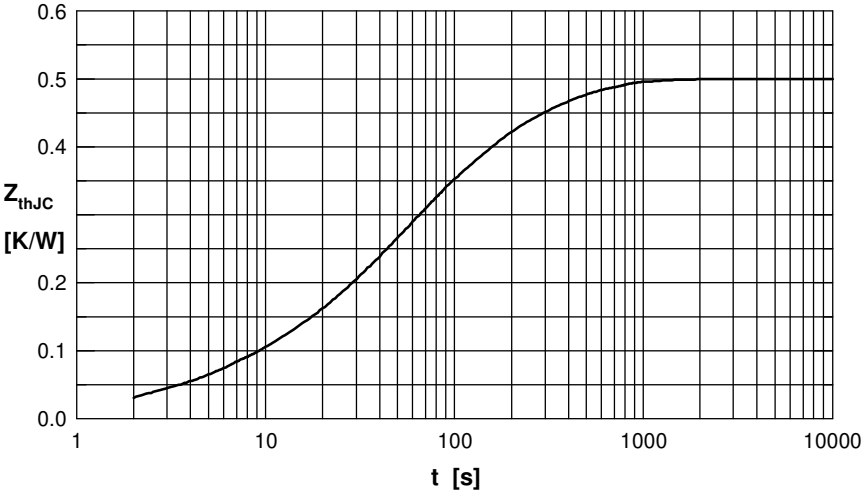

Fig. 6 Transient thermal impedance junction to case vs. time per diode

Constants for Z_{thJC} calculation:

i	R_{th} (K/W)	t_i (s)
1	0.040	0.004
2	0.003	0.010
3	0.140	0.030
4	0.120	0.300
5	0.197	0.080

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Brake IGBT + Diode

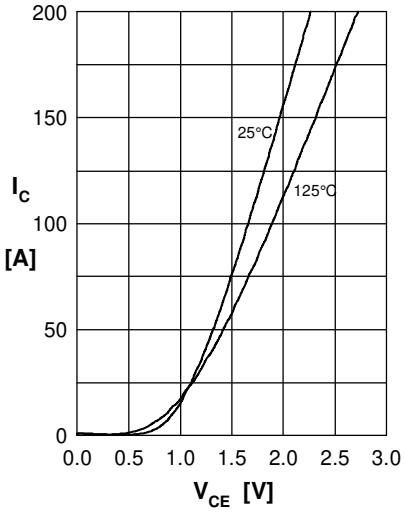

Fig.1 Output characteristics IGBT

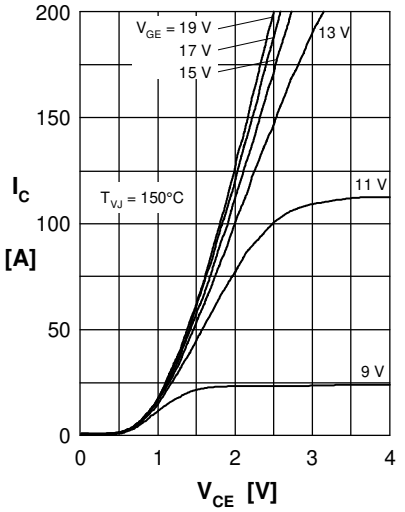

Fig.2 Typ. output characteristics IGBT

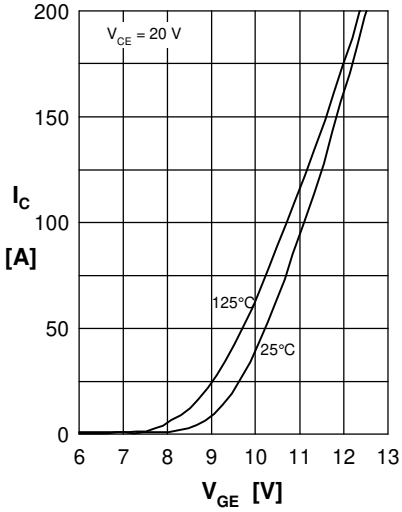

Fig. 3 Typ. transfer charact. IGBT

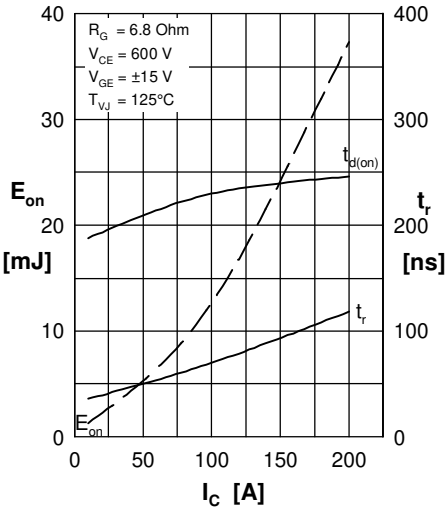

Fig. 4 Typ. turn-on energy & switch. times vs. collector current

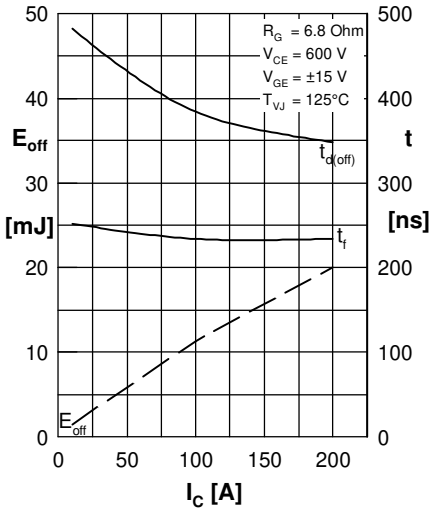

Fig. 5 Typ. turn-off energy & switch. times vs. collector current

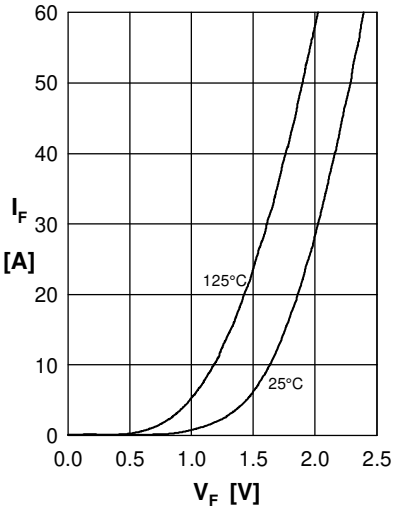

Fig. 6 Typ. forward characteristics Diode

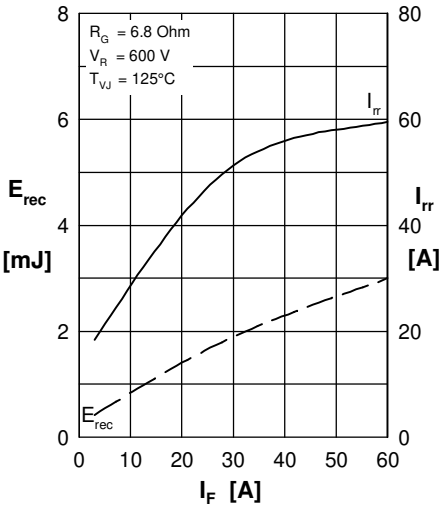

Fig. 7 Typ. reverse recovery characteristics Diode

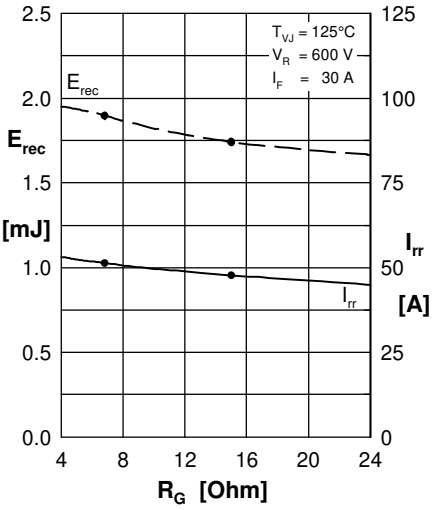

Fig. 8 Typ. reverse recovery characteristics Diode

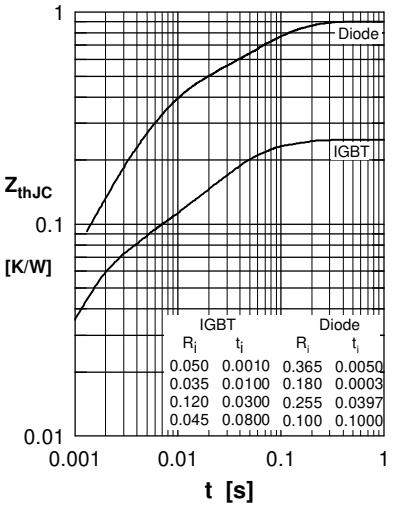

Fig. 9 Transient thermal resistance junction to case

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